



**THE DATASHEET OF  
NVB5860NLT4G**



# NTB5860NL, NTP5860NL, NVB5860NL



ON Semiconductor®

<http://onsemi.com>

## N-Channel Power MOSFET

60 V, 220 A, 3.0 mΩ

### Features

- Low  $R_{DS(on)}$
- High Current Capability
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant
- NVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ Unless otherwise specified)

| Parameter   | Symbol    | Value                     | Unit             |
|---|-----------|---------------------------|------------------|
| Drain-to-Source Voltage   | $V_{DSS}$ | 60                        | V                |
| Gate-to-Source Voltage – Continuous                                     | $V_{GS}$  | $\pm 20$                  | V                |
| Continuous Drain Current, $R_{\theta JC}$                               | $I_D$     | $T_A = 25^\circ\text{C}$  | 220              |
|   |           | $T_A = 100^\circ\text{C}$ | 156              |
| Power Dissipation, $R_{\theta JC}$                                      | $P_D$     | 283                       | W                |
| Pulsed Drain Current  | $I_{DM}$  | 660                       | A                |
| Current Limited by Package  |           | $I_{DMmax}$               | 130              |
| Operating and Storage Temperature Range                                 |           | $T_J, T_{stg}$            | -55 to +175      |
| Source Current (Body Diode)   | $I_S$     | 130                       | A                |
| Single Pulse Drain-to-Source Avalanche Energy ( $L = 0.3$ mH)           | $E_{AS}$  | 735                       | mJ               |
| Lead Temperature for Soldering Purposes (1/8" from Case for 10 Seconds) | $T_L$     | 260                       | $^\circ\text{C}$ |

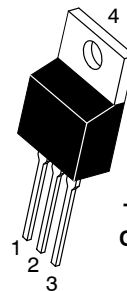
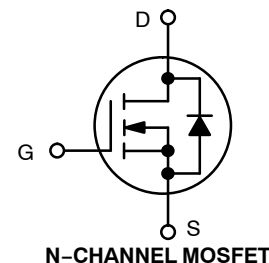
### THERMAL RESISTANCE RATINGS

| Parameter                                   | Symbol          | Max  | Unit                      |
|---|-----------------|------|---------------------------|
| Junction-to-Case (Drain) Steady State       | $R_{\theta JC}$ | 0.53 | $^\circ\text{C}/\text{W}$ |
| Junction-to-Ambient – Steady State (Note 1) | $R_{\theta JA}$ | 28   |                           |

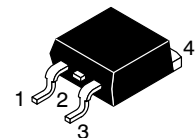
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).

| $V_{(BR)DSS}$ | $R_{DS(on)}$ MAX | $I_D$ MAX |
|---------------|------------------|-----------|
| 60 V          | 3.0 mΩ @ 10 V    | 220 A     |
|               | 3.6 mΩ @ 4.5 V   |           |

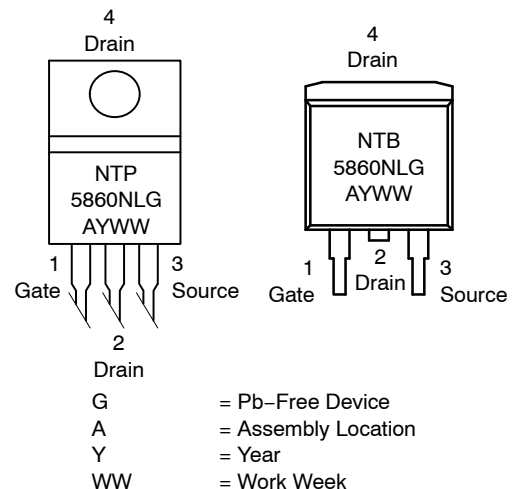


TO-220AB  
CASE 221A  
STYLE 5



D2PAK  
CASE 418B  
STYLE 2

### MARKING DIAGRAMS & PIN ASSIGNMENTS



### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# NTB5860NL, NTP5860NL, NVB5860NL

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C Unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------------|--------|----------------|-----|-----|-----|------|
|-----------------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|   |                                      |   |                        |     |      |       |
|---|--------------------------------------|---|------------------------|-----|------|-------|
| Drain-to-Source Breakdown Voltage                         | V <sub>(BR)DSS</sub>                 | V <sub>DS</sub> = 0 V, I <sub>D</sub> = 250 μA  | 60                     |     |      | V     |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V <sub>(BR)DSS</sub> /T <sub>J</sub> | I <sub>D</sub> = 250 μA                         |                        | 6.1 |      | mV/°C |
| Zero Gate Voltage Drain Current                           | I <sub>DSS</sub>                     | V <sub>GS</sub> = 0 V<br>V <sub>DS</sub> = 60 V | T <sub>J</sub> = 25°C  |     | 1.0  | μA    |
|   |                                      | V <sub>GS</sub> = 0 V<br>V <sub>DS</sub> = 60 V | T <sub>J</sub> = 125°C |     | 100  |       |
| Gate-Source Leakage Current                               | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V  |                        |     | ±100 | nA    |

### ON CHARACTERISTICS (Note 2)

|                                   |                                     |   |     |      |     |       |
|-----------------------------------|-------------------------------------|---|-----|------|-----|-------|
| Gate Threshold Voltage            | V <sub>GS(th)</sub>                 | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA | 1.0 |      | 3.0 | V     |
| Threshold Temperature Coefficient | V <sub>GS(th)</sub> /T <sub>J</sub> |   |     | -7.7 |     | mV/°C |
| Drain-to-Source On-Resistance     | R <sub>DS(on)</sub>                 | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A               |     | 2.4  | 3.0 | mΩ    |
|                                   |                                     | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A              |     | 2.8  | 3.6 |       |
| Forward Transconductance          | g <sub>FS</sub>                     | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A               |     | 47   |     | S     |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                       |                     |  |  |       |  |    |
|-----------------------|---------------------|--|--|-------|--|----|
| Input Capacitance     | C <sub>iss</sub>    | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,<br>f = 1 MHz              |  | 13216 |  | pF |
| Output Capacitance    | C <sub>oss</sub>    |  |  | 1127  |  |    |
| Transfer Capacitance  | C <sub>rss</sub>    |  |  | 752   |  |    |
| Total Gate Charge     | Q <sub>G(TOT)</sub> | V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 48 V,<br>I <sub>D</sub> = 40 A |  | 220   |  | nC |
| Threshold Gate Charge | Q <sub>G(TH)</sub>  |  |  | 13    |  |    |
| Gate-to-Source Charge | Q <sub>GS</sub>     |  |  | 37    |  |    |
| Gate-to-Drain Charge  | Q <sub>GD</sub>     |  |  | 54    |  |    |

### SWITCHING CHARACTERISTICS, V<sub>GS</sub> = 10 V (Note 3)

|                     |                     |   |  |     |  |    |
|---------------------|---------------------|---|--|-----|--|----|
| Turn-On Delay Time  | t <sub>d(on)</sub>  | V <sub>GS</sub> = 10 V, V <sub>DD</sub> = 48 V,<br>I <sub>D</sub> = 100 A, R <sub>G</sub> = 2.5 Ω |  | 25  |  | ns |
| Rise Time           | t <sub>r</sub>      |   |  | 58  |  |    |
| Turn-Off Delay Time | t <sub>d(off)</sub> |   |  | 98  |  |    |
| Fall Time           | t <sub>f</sub>      |   |  | 144 |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                                |                 |   |                        |    |      |     |                 |
|--------------------------------|-----------------|---|------------------------|----|------|-----|-----------------|
| Forward Diode Voltage          | V <sub>SD</sub> | V <sub>GS</sub> = 0 V<br>I <sub>S</sub> = 40 A                                  | T <sub>J</sub> = 25°C  |    | 0.76 | 1.1 | V <sub>dc</sub> |
|                                |                 |   | T <sub>J</sub> = 125°C |    | 0.60 |     |                 |
| Reverse Recovery Time          | t <sub>rr</sub> | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 100 A,<br>dI <sub>S</sub> /dt = 20 A/μs |                        | 50 |      | ns  |                 |
| Charge Time                    | t <sub>a</sub>  |   |                        | 25 |      |     |                 |
| Discharge Time                 | t <sub>b</sub>  |   |                        | 25 |      |     |                 |
| Reverse Recovery Stored Charge | Q <sub>RR</sub> |   |                        | 71 |      |     | nC              |

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

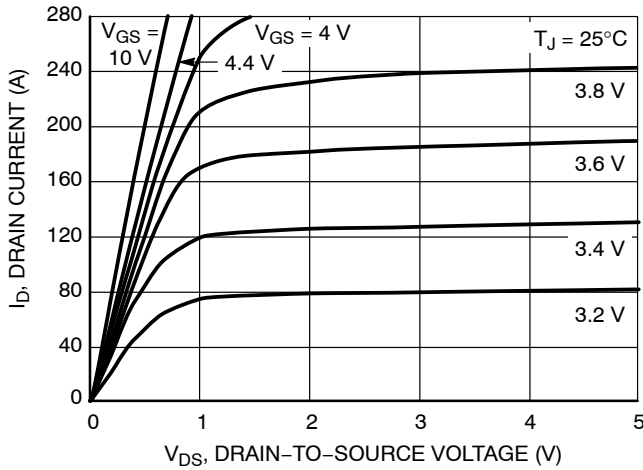


Figure 1. On-Region Characteristics

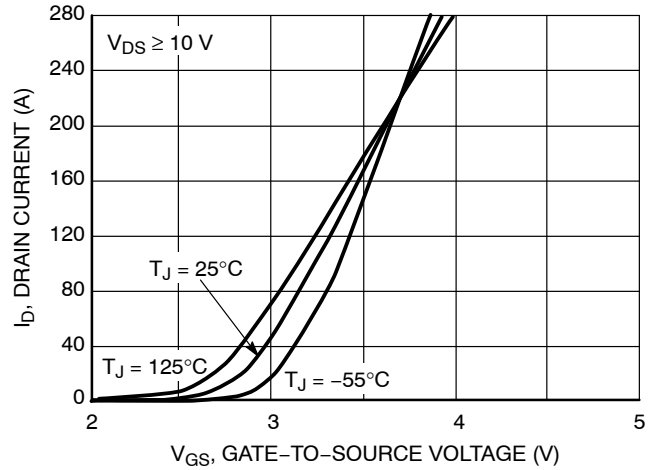


Figure 2. Transfer Characteristics

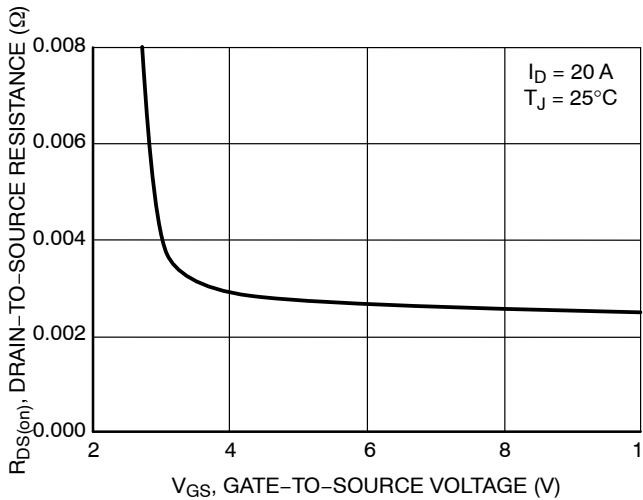


Figure 3. On-Resistance vs. Gate Voltage

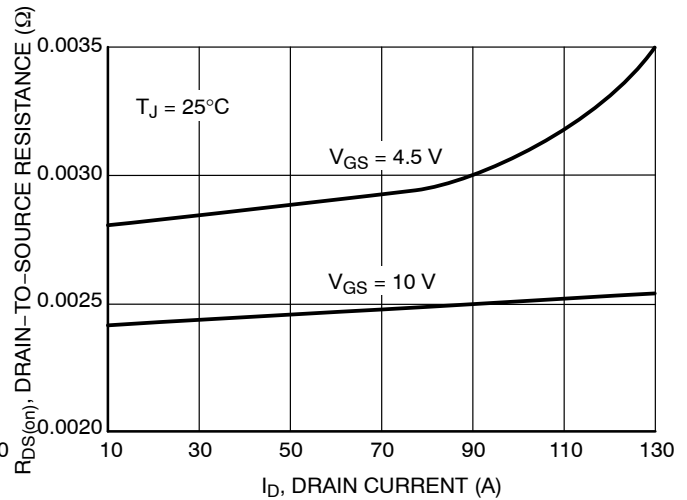


Figure 4. On-Resistance vs. Drain Current

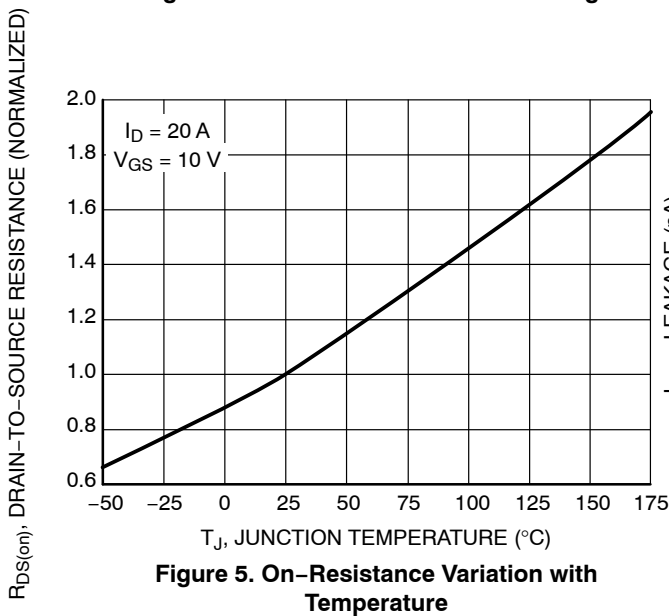


Figure 5. On-Resistance Variation with Temperature

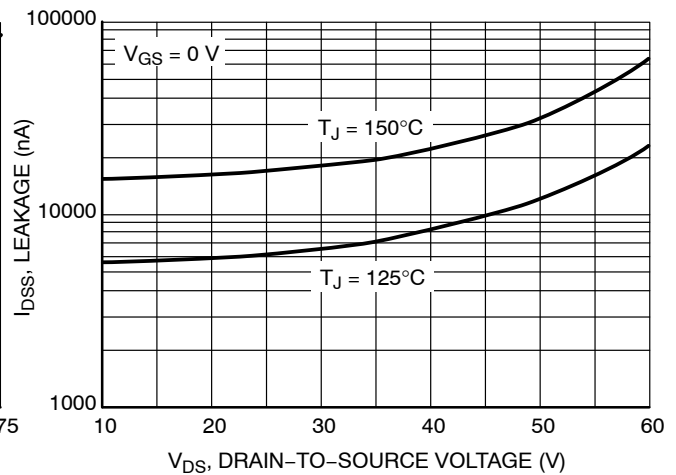


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

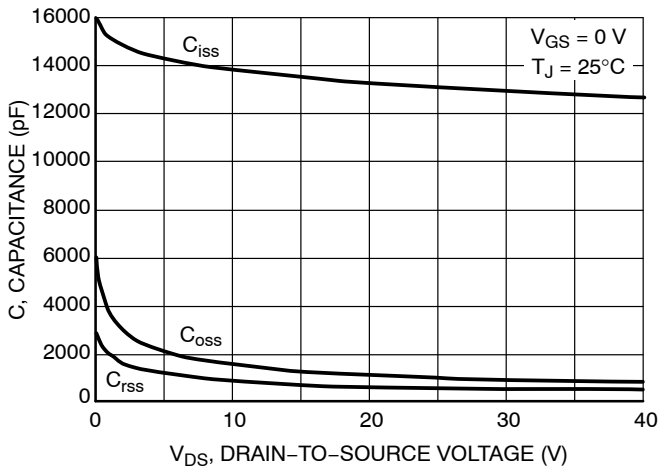


Figure 7. Capacitance Variation

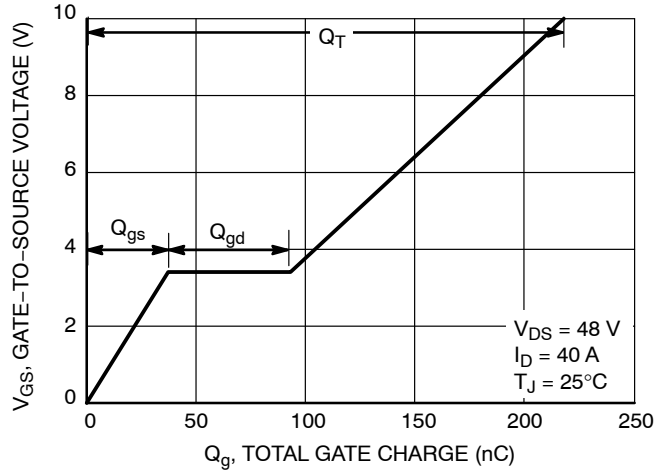


Figure 8. Gate-to-Source vs. Total Charge

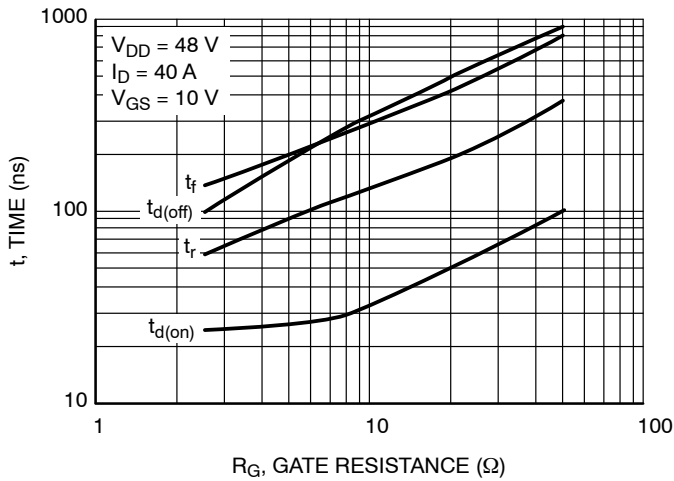


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

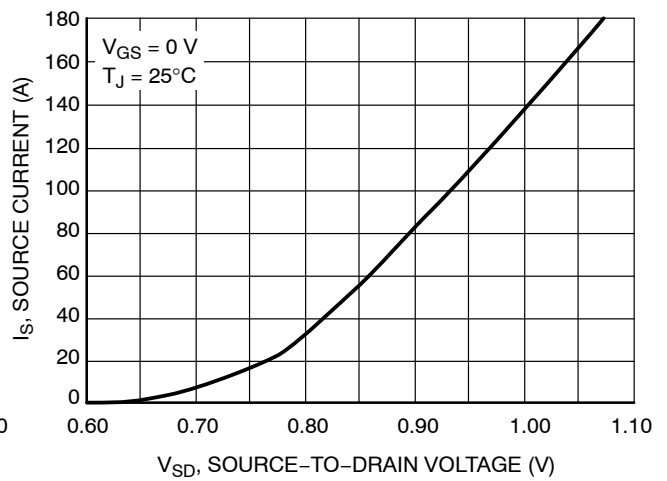


Figure 10. Diode Forward Voltage vs. Current

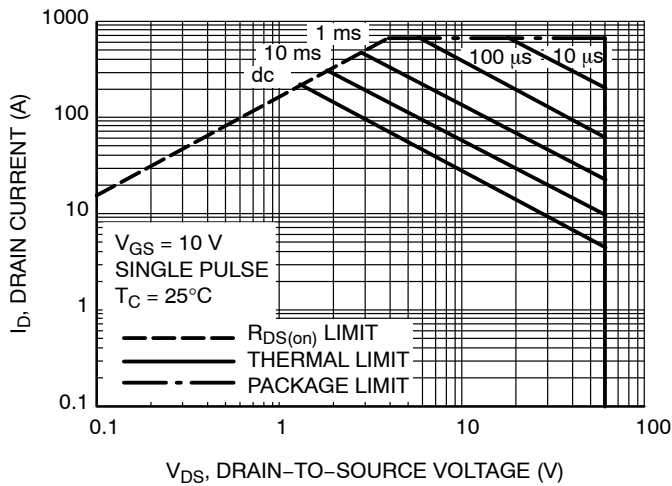


Figure 11. Maximum Rated Forward Biased Safe Operating Area

# NTB5860NL, NTP5860NL, NVB5860NL

## TYPICAL CHARACTERISTICS

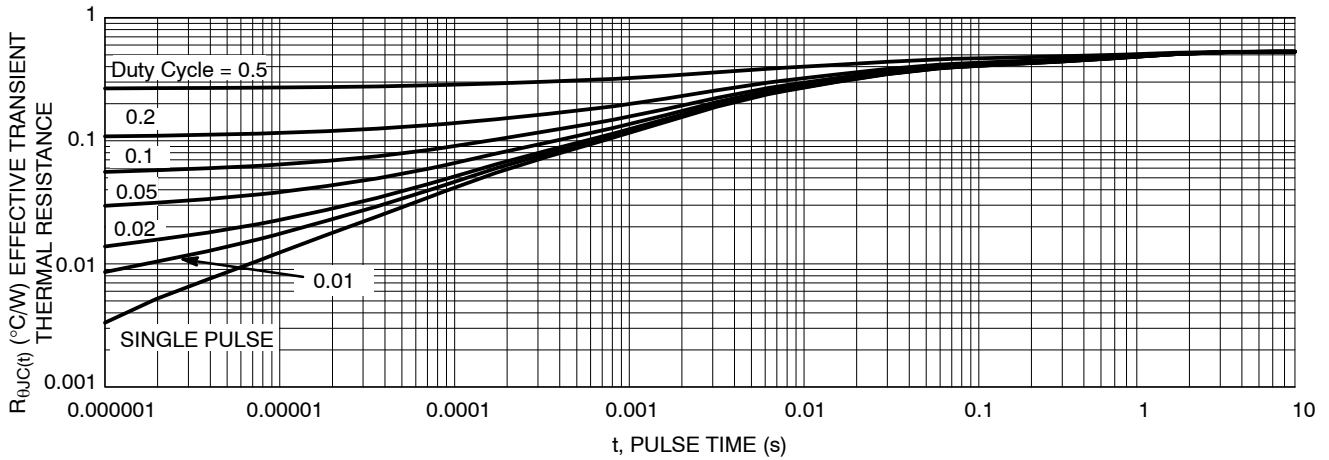


Figure 12. Thermal Response

### ORDERING INFORMATION

| Device        | Package                         | Shipping <sup>†</sup> |
|---------------|---------------------------------|-----------------------|
| NTP5860NLG    | TO-220AB<br>(Pb-Free)           | 50 Units / Rail       |
| NTB5860NLT4G  | D <sup>2</sup> PAK<br>(Pb-Free) | 800 / Tape & Reel     |
| NVB5860NLT4G* | D <sup>2</sup> PAK<br>(Pb-Free) | 800 / Tape & Reel     |

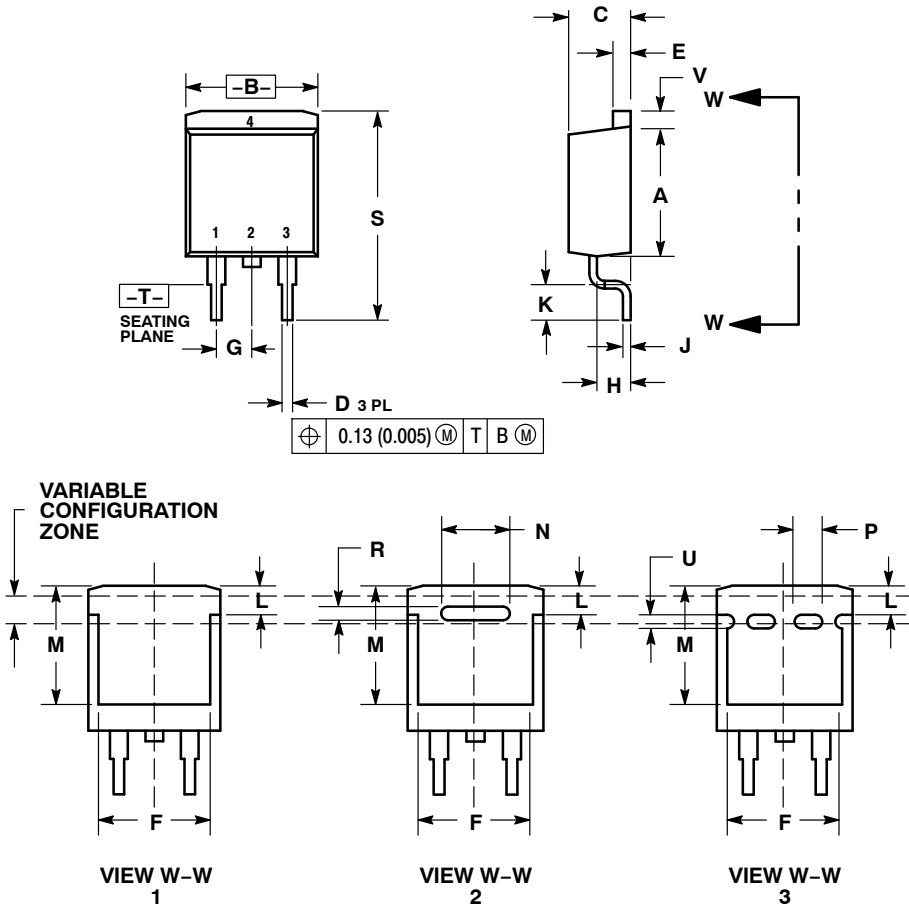
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

# NTB5860NL, NTP5860NL, NVB5860NL

## PACKAGE DIMENSIONS

D<sup>2</sup>PAK  
CASE 418B-04  
ISSUE J

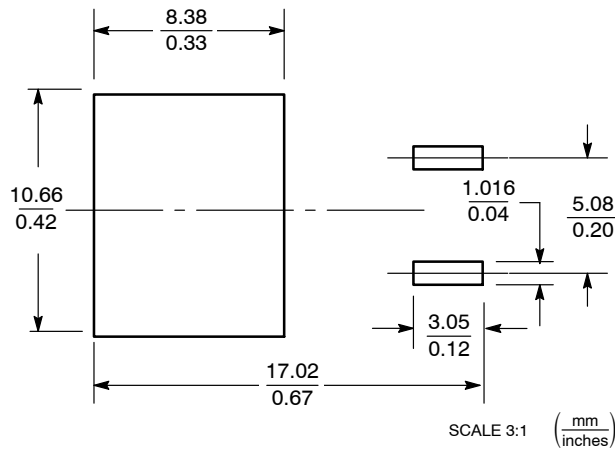


- NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.  
 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 0.340  | 0.380 | 8.64        | 9.65  |
| B   | 0.380  | 0.405 | 9.65        | 10.29 |
| C   | 0.160  | 0.190 | 4.06        | 4.83  |
| D   | 0.020  | 0.035 | 0.51        | 0.89  |
| E   | 0.045  | 0.055 | 1.14        | 1.40  |
| F   | 0.310  | 0.350 | 7.87        | 8.89  |
| G   | 0.100  | BSC   | 2.54        | BSC   |
| H   | 0.080  | 0.110 | 2.03        | 2.79  |
| J   | 0.018  | 0.025 | 0.46        | 0.64  |
| K   | 0.090  | 0.110 | 2.29        | 2.79  |
| L   | 0.052  | 0.072 | 1.32        | 1.83  |
| M   | 0.280  | 0.320 | 7.11        | 8.13  |
| N   | 0.197  | REF   | 5.00        | REF   |
| P   | 0.079  | REF   | 2.00        | REF   |
| R   | 0.039  | REF   | 0.99        | REF   |
| S   | 0.575  | 0.625 | 14.60       | 15.88 |
| V   | 0.045  | 0.055 | 1.14        | 1.40  |

- STYLE 2:  
 PIN 1. GATE  
 2. DRAIN  
 3. SOURCE  
 4. DRAIN

### SOLDERING FOOTPRINT\*

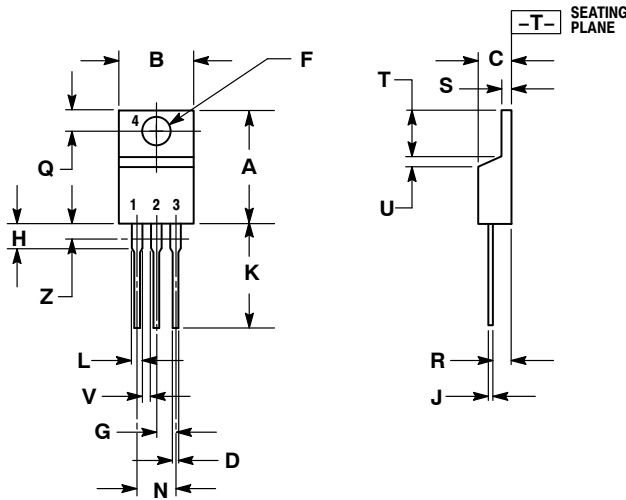


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NTB5860NL, NTP5860NL, NVB5860NL

## PACKAGE DIMENSIONS

### TO-220 CASE 221A-09 ISSUE AF



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN    | MAX   | MIN         | MAX   |
| A   | 0.570  | 0.620 | 14.48       | 15.75 |
| B   | 0.380  | 0.405 | 9.66        | 10.28 |
| C   | 0.160  | 0.190 | 4.07        | 4.82  |
| D   | 0.025  | 0.035 | 0.64        | 0.88  |
| F   | 0.142  | 0.161 | 3.61        | 4.09  |
| G   | 0.095  | 0.105 | 2.42        | 2.66  |
| H   | 0.110  | 0.155 | 2.80        | 3.93  |
| J   | 0.014  | 0.025 | 0.36        | 0.64  |
| K   | 0.500  | 0.562 | 12.70       | 14.27 |
| L   | 0.045  | 0.060 | 1.15        | 1.52  |
| N   | 0.190  | 0.210 | 4.83        | 5.33  |
| Q   | 0.100  | 0.120 | 2.54        | 3.04  |
| R   | 0.080  | 0.110 | 2.04        | 2.79  |
| S   | 0.045  | 0.055 | 1.15        | 1.39  |
| T   | 0.235  | 0.255 | 5.97        | 6.47  |
| U   | 0.000  | 0.050 | 0.00        | 1.27  |
| V   | 0.045  | ---   | 1.15        | ---   |
| Z   | ---    | 0.080 | ---         | 2.04  |

STYLE 5:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### PUBLICATION ORDERING INFORMATION

**LITERATURE FULFILLMENT:**

Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
Email: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)

**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative

## Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

 [View NVB5860NLT4G on WIN SOURCE](#)

 [ON Semiconductor](#) Information

## Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management